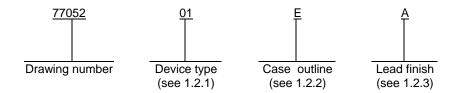
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LTR						DESCR	RIPTIOI	N					D/	DATE (YR-MO-DA)			APPROVED			
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Н	Char	iges in	accord	lance w	ith NO	R 5962	2-R135-	-95.						95-0	95-05-09 M. A. F			. Frye		
J	Draw – drw		dated to	o reflec	t curre	nt requ	iremen	ts. Edi	torial cl	changes throughout.				00-0	08-23		R. Monnin			
К	Drawing updated to current requirements. Editorial change					hanges	throug	jhout. –	- drw		03-0)2-04		R. Monnin						
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THE ORIGINAL					RAWIN	IG HAS	BEEN	I REPL	ACED.											
THE ORIGINAL REV	L FIRST	SHEE			RAWIN	IG HAS	SBEEN	I REPL	ACED.											
REV SHEET REV	L L 15	SHEE				IG HAS	S BEEN	I REPL	ACED.	L	L	L	L	L	L	L	L	L	L	L
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REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	L FIRST	L 16		REV SHE PREI	EET PAREI	D BY	L	L	L	L	5	6 EFEN	7 SE S	8 UPPL	9 .Y CE	10	11 COL	12 .UMB	13	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	L L 15	L 16		REV SHE PREI A	PAREI J. Fole CKED R. Jack	D BY y BY sson	L	L	L	L	5	6 EFEN	7 ISE SI	8 UPPL IBUS,	9 .Y CE	10	11 R COL 218-39	12 .UMB	13	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DR/ THIS DRAWII FOR U DEPA	NDAF DCIRO AWIN	L 16 CUIT G VAILARALL TS	T OF T	REV SHE PREI A	PROVE A. Haud	D BY y BY son	L 1	L 2	L	L 4 MIC 8-C	DI CROC	EFEN CO	7 SE SI OLUM http	UPPLIBUS, D://ww	9 Y CE , OHIO , W.ds	10 ENTER O 432 SCC.dl	11 R COL 218-39 a.mil	12 -UMB 990	13 US	14
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DR/ THIS DRAWII FOR U DEPARTMEN	NDAF OCIRC AWIN NG IS A ISE BY NCIES ONT OF I	L 16 CUIT G VAILARALL TS DF THE DEFEN	T OF T	REV SHE PREI A	PROVE A. Haud	D BY y BY son D BY ck	L 1	L 2	L	L 4 MIC 8-C	DI CROC	EFEN CO	7 SE SI OLUM http	UPPLIBUS, D://ww	9 Y CE, OHIO W.ds S, PC EXEF	10 ENTER O 432 SCC.dl	11 R COL 218-39 a.mil	12 -UMB 990	13 US	14
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DR/ THIS DRAWII FOR U DEPARTMEN	NDAF OCIRCAWING IS A SE BY A RTMEN NCIES (L 16 CUIT G VAILARALL TS DF THE DEFEN	T OF T	REV SHE PREI A	CKED CKED R. Jack	D BY y BY son D BY ck APPRO 77-1	DVAL E 0-26	L 2	L	L 4 MIC 8-C MC	DI CROC	EFEN CO CIRCI NEL ITHIC	7 SE SI OLUM http	BUPPLIBUS: D://ww	9 Y CE, OHIO W.ds S, PC EXEF	10 ENTER O 432 SCC.dl	218-33 a.mil	12 -UMB 990	13 US	14

1. SCOPE

- 1.1 <u>Scope</u>. This drawing describes device requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A.
 - 1.2 Part or Identifying Number (PIN). The complete PIN is as shown in the following example:



1.2.1 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	DG508A, HI-508, ADG508A	CMOS, positive logic, 8-channel analog MUX/DEMUX
02	HI-508A, HI-548	CMOS, positive logic, 8-channel analog MUX/DEMUX with overvoltage protection
03	MAX358	CMOS, positive logic, 8-channel analog MUX/DEMUX with overvoltage protection

1.2.2 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
2	CQCC1-N20	20	Square leadless chip carrier
Е	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
F	GDFP2-F16 or CDFP3-F16	16	Flat pack
Χ	CDFP4-F16	16	Flat pack

- 1.2.3 Lead finish. The lead finish is as specified in MIL-PRF-38535, appendix A.
- 1.3 Absolute maximum ratings.

Supply voltage between V+ and V-:	. 4437 -1-
Device type 01	
Device types 02 and 03	+40 V dc
V+ to ground:	
Device type 01	+22 V dc
Device types 02 and 03	+20 V dc
V- to ground:	
Device type 01	-22 V dc
Device types 02 and 03	-20 V dc
Digital input overvoltage range:	
Device types 02 and 03	(V-) - 4.0 V dc to $(V+)$ + 4.0 V dc
Analog input overvoltage range:	
Device type 01	(V-) - 3.0 V dc to (V+)
Analog input voltage (V _S):	
Device type 01	$(V_{-}) = 2 V dc to (V_{+}) + 2 V dc$
Device types 02 and 03	
Device types 02 and 03	(v-) - 20 v dc to (v+) + 20 v dc

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1.3 Absolute maximum ratings – continued.

Storage temperature range-65°C to +150°C

Power dissipation (PD):

Case 2 $1.23 \text{ W at T}_{A} = +75^{\circ}\text{C}$ Case E $470 \text{ mW at T}_{A} = +75^{\circ}\text{C}$

Derating factor:

Lead temperature (soldering, 10 seconds)+300°C Junction temperature (T_J)+175°C

1.4 Recommended operating conditions.

Logic low level address input voltage (VIL) 0 V dc to 0.8 V dc

Logic high level address input voltage (VIH):

Device types 01 and 03 2.4 V dc to (V+) - 0.7 V dc

Device type 02 4.0 V dc to V+

Enable voltage (V_{EN}):

Ambient operating temperature range (T_A) -55°C to +125°C

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or http://assist.daps.dla.mil or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

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2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein. Product built to this drawing that is produced by a Qualified Manufacturer Listing (QML) certified and qualified manufacturer or a manufacturer who has been granted transitional certification to MIL-PRF-38535 may be processed as QML product in accordance with the manufacturers approved program plan and qualifying activity approval in accordance with MIL-PRF-38535. This QML flow as documented in the Quality Management (QM) plan may make modifications to the requirements herein. These modifications shall not affect form, fit, or function of the device. These modifications shall not affect the PIN as described herein. A "Q" or "QML" certification mark in accordance with MIL-PRF-38535 is required to identify when the QML flow option is used.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535, appendix A and herein.
 - 3.2.1 <u>Case outlines</u>. The case outlines shall be in accordance with 1.2.2 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Truth table. The truth table shall be as specified on figure 2.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.
- 3.5 <u>Marking</u>. Marking shall be in accordance with MIL-PRF-38535, appendix A. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked.
- 3.5.1 <u>Certification/compliance mark</u>. A compliance indicator "C" shall be marked on all non-JAN devices built in compliance to MIL-PRF-38535, appendix A. The compliance indicator "C" shall be replaced with a "Q" or "QML" certification mark in accordance with MIL-PRF-38535 to identify when the QML flow option is used.
- 3.6 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-PRF-38535, appendix A and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
 - 3.8 Notification of change. Notification of change to DSCC-VA shall be required for any change that affects this drawing.
- 3.9 <u>Verification and review</u>. DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

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TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions $1/$ V- = -15 V, V+ = +15 V, V _{EN} = 4.5 V	Group A subgroups	Device type	Li	mits	Unit
		-55°C ≤ T _A ≤ +125°C unless otherwise specified			Min	Max	
Input leakage current 2/	ΙΗ	Measure address inputs sequentially, connect all	1,2	01		+0.8	μА
	I _{ΙL}	unused address inputs to 5.0 V				-0.8	
Leakage current into the source terminal of an	+IS(OFF)	$V_S = +10 \text{ V}, V_{EN} = 0.8 \text{ V},$ all unused inputs = -10 V	1,2,3	01	-50	+50	nA
"OFF" switch	-I _{S(OFF)}	$V_S = -10 \text{ V}, V_{EN} = 0.8 \text{ V},$ all unused inputs = +10 V					
Leakage current into the drain terminal of an	+I _{D(OFF)}	$V_D = +10 \text{ V}, V_{EN} = 0.8 \text{ V},$ all unused inputs = -10 V	1,2,3	01	-250	+250	nA
"OFF" switch	-I _{D(OFF)}	$V_D = -10 \text{ V}, V_{EN} = 0.8 \text{ V},$ all unused inputs = +10 V					
Leakage current from an "ON" driver into the	+I _{D(ON)}	$V_D = +10 \text{ V}, V_S = -10 \text{ V},$ all unused inputs = -10 V	1,2,3	01	-250	+250	nA
switch (drain)	-I _{D(ON)}	$V_D = -10 \text{ V}, V_S = +10 \text{ V},$ all unused inputs = +10 V					
Positive supply current	l(+)	V _A = 0 V, V _{EN} = 5 V	1,2,3	01		+12	mA
Negative supply current	I(-)	V _A = 0 V, V _{EN} = 5 V	1,2,3	01	-12		mA
Standby positive supply current	+I _{SBY}	V _A = 0 V, V _{EN} = 0 V	1, 2, 3	01		+3.5	mA
Standby negative supply current	-I _{SBY}	V _A = 0 V, V _{EN} = 0 V	1, 2, 3	01	-3.5		mA
Switch "ON" resistance	R _{DS1}	V _S = +10 V, I _D = +1 mA	1, 3	01		400	Ω
			2			500	
		V _S = -10 V, I _D = -1 mA	1, 3			400]
			2	-		500	1
Switch "ON" resistance	R _{DS2}	V+ = +10 V, V- = -10 V, V _S = +7.5 V, I _D = -1 mA	1, 2, 3	01		1000	Ω
		V+ = +10 V, V- = +10 V, V _S = -7.5 V, I _D = -1 mA				1000	

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TABLE I. <u>Electrical performance characteristics</u> – continued.

Test	Symbol	Conditions $1/$ V- = -15 V, V+ = +15 V, V _{EN} = 4.5 V	Group A subgroups	Device type	Liı	mits	Unit
		-55°C ≤ T _A ≤ +125°C unless otherwise specified			Min	Max	-
Capacitance: Address	C _A	$V+ = V- = 0 V, \underline{3}/$ $f = 1 MHz, T_A = +25^{\circ}C$	4	01		10	pF
Capacitance: output switch	Cos	V+ = V- = 0 V, <u>3</u> / f = 1 MHz, T _A = +25°C	4	01		45	pF
Capacitance: input switch	C _{IS}	V+ = V- = 0 V, $3/f = 1 MHz, T_A = +25°C$	4	01		10	pF
Charge transfer error	VCTE	$V_S = GND$, $3/$ $V_{GEN} = 0 V \text{ to 5 V}$, $f = 500 \text{ kHz}$, $C_L = 100 \text{ pF}$, $T_A = +25^{\circ}\text{C}$	4	01		10	mV
Single channel isolation	V _{ISO}	$V_{GEN} = 1 V_{P-P}, 3/$ $f = 200 \text{ kHz}, T_A = +25^{\circ}\text{C}$	4	01	50		dB
Crosstalk between channels	Vст	V _{GEN} = 1 V _{P-P} , <u>3/</u> f = 200 kHz, T _A = +25°C	4	01	50		dB
Break-before-make time delay	t _D	T _A = +25°C, see figure 3	9	01	5		ns
Propagation delay times: Address inputs to	t _{ON(A)}	$R_L = 1 \text{ k}\Omega, C_L = 100 \text{ pF},$	9, 11	01		1000	ns
I/O channels	t _{OFF(A)}	see figure 4	10			1500	
Enable to I/O	t _{ON(EN)}	$R_L = 1 \text{ k}\Omega, C_L = 100 \text{ pF},$	9, 11	01		1000	ns
	tOFF(EN)	see figure 5	10			1500	

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Test	Symbol	Conditions $1/$ V- = -15 V, V+ = +15 V, V _{EN} = 4.0 V	Group A subgroups	Device type			Unit
		-55°C ≤ T _A ≤ +125°C unless otherwise specified			Min	Max	
Positive input clamping voltage	V _{IC(POS)}	$I_{IN} = 1 \text{ mA}, \underline{3}/$ V+ = V- = 0 V, T _A = +25°C	1	02		+1.5	V
Negative input clamping voltage	VIC(NEG)	$I_{IN} = -1 \text{ mA}, \underline{3}/$ V+ = V- = 0 V, T _A = +25°C	1	02	-1.5		V
Input leakage current 2/	lін	Measure inputs sequentially, connect all	1,2	02	-1.0	+1.0	μА
	IIL	unused inputs to GND			+1.0	-1.0	
Leakage current into the source terminal of an "OFF" switch	+IS(OFF)	$V_S = +10 \text{ V}, V_{EN} = 0.8 \text{ V},$ $V_D = -10 \text{ V},$ all unused inputs = -10 V	1,2	02	-50	+50	nA
	-I _{S(OFF)}	$V_S = -10 \text{ V}, V_{EN} = 0.8 \text{ V},$ $V_D = +10 \text{ V},$ all unused inputs = +10 V					
Leakage current into the drain terminal of an	+I _{D(OFF)}	$V_D = +10 \text{ V}, V_{EN} = 0.8 \text{ V},$ all unused inputs = -10 V	1,2	02	-250	+250	nA
"OFF" switch	-I _{D(OFF)}	$V_D = -10 \text{ V}, V_{EN} = 0.8 \text{ V},$ all unused inputs = +10 V					
Leakage current from an "ON" driver into the	+I _{D(ON)}	$V_D = +10 \text{ V}, V_S = +10 \text{ V},$ all unused inputs = -10 V	1,2,3	02	-250	+250	nA
switch (drain)	-I _{D(ON)}	$V_D = -10 \text{ V}, V_S = -10 \text{ V},$ all unused inputs = +10 V					
Overvoltage protected, leakage current into the drain terminal of an "OFF" switch	tage protected, e current into the $V_S = +33 \text{ V}, V_D = 0 \text{ V},$ 1,2,3	02	-2.0	+2.0	μА		
	-I _{D(OFF)} over- voltage	$V_S = -33 \text{ V}, V_D = 0 \text{ V},$ $V_{EN} = 0.8 \text{ V}$					
Positive supply current	l(+)	V _A = 0 V, V _{EN} = 4 V	1,2,3	02		+2.0	mA
Negative supply current	I(-)	V _A = 0 V, V _{EN} = 4 V	1,2,3	02	-1.0		mA
Standby positive supply current	+I _{SBY}	V _A = 0 V, V _{EN} = 0 V	1, 2, 3	02		+2.0	mA
				1		l	

Standby negative supply current

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 $V_A = 0 V$, $V_{EN} = 0 V$

-I_{SBY}

02

1, 2, 3

-1.0

mΑ

	TABL	E I. Electrical performance chara	acteristics – co	ntinued.			
Test	Symbol	Conditions $\underline{1}/$ V- = -15 V, V+ = +15 V, VEN = 4.0 V	Group A subgroups	Device type	Limits		Unit
		-55°C ≤ T _A ≤ +125°C unless otherwise specified			Min	Max	
Switch "ON" resistance	+R _{DS1}	$V_S = +10 \text{ V}, I_D = -100 \mu\text{A}$	1	02		1500	Ω
			2,3			1800	
	-R _{DS1}	$V_S = -10 \text{ V}, I_D = -100 \mu\text{A}$	1			1500	Ω
			2,3	-		1800	_
Difference in switch "ON" resistance between channels	+∆RDS1	$(+R_{DS1} \text{ max}) - (+R_{DS1} \text{ min}) \text{ x}$ $100 / +R_{DS1} \text{ AVE},$ $T_A = +25^{\circ}\text{C}$	1	02		7	%
	-∆R _{DS1}	$(-R_{DS1} \text{ max}) - (-R_{DS1} \text{ min}) \text{ x}$ $100 / -R_{DS1} \text{ AVE},$ $T_A = +25^{\circ}\text{C}$	1			7	-
Capacitance: Address	СА	V+ = V- = 0 V, <u>3</u> / f = 1 MHz, T _A = +25°C	4	02		10	pF
Capacitance: output switch	Cos	V+ = V- = 0 V, <u>3</u> / f = 1 MHz, T _A = +25°C	4	02		45	pF
Capacitance: input switch	C _{IS}	V+ = V- = 0 V, <u>3</u> / f = 1 MHz, T _A = +25°C	4	02		15	pF
Charge transfer error	VCTE	$V_S = GND$, $3/$ $V_{GEN} = 0 V to 5 V$, $T_A = +25^{\circ}C$	4	02		10	mV
Off isolation	Viso	$V_{GEN} = 0.8 \text{ Vp-p}, \qquad \underline{3}/$ $f = 100 \text{ kHz}, V_S = 7 \text{ V rms},$ $R_L = 1 \text{ k}\Omega, C_L = 15 \text{ pF},$ $T_A = +25^{\circ}\text{C}$	4	02	50		dB
Break-before-make time delay	t _D	$R_L = 1 \text{ k}\Omega$, $C_L = 12.5 \text{ pF}$, $3/$ $T_A = +25^{\circ}\text{C}$, see figure 3	9	02	5		ns
Propagation delay times: Address inputs to	tON(A)	$R_L = 1 M\Omega$, $C_L = 14 pF$,	9	02		500	ns
I/O channels	tOFF(A)	see figure 4	10,11	-		1000	-
Enable to I/O	tON(EN)	$R_L = 1 \text{ k}\Omega, C_L = 12.5 \text{ pF},$	9	02		500	ns
	t _{OFF} (EN)	see figure 5	10,11	-		1000	1

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TABLE	I. Electrical performance chara	<u>acteristics</u> – cor	ntinued.

Test	Symbol	Conditions $1/V = -15 V, V = +15 V, V = 2.4 V$	Group A subgroups	Device type	Limits		Unit
		-55°C ≤ T _A ≤ +125°C unless otherwise specified			Min	Max	
Input leakage current 2/	ΙΗ	Measure inputs sequentially, connect all	1	03	-1.0	1.0	μΑ
		unused inputs to ground	2			10	
	IIL		1		-1.0	1.0	
			2			10	
		V _S = +10 V, V _{EN} = 0.8 V,	1,2,3	03	-50	+50	nA
Leakage current into the source terminal of an	I _{S(OFF)}	V _D = -10 V, all unused inputs = -10 V					
"OFF" switch		$V_S = -10 \text{ V}, V_{EN} = 0.8 \text{ V},$					
		V _D = +10 V, all unused inputs = +10 V					
Leakage current into the drain terminal of an	+I _{D(OFF)}	$V_D = +10 \text{ V}, V_{EN} = 0.8 \text{ V},$ all unused inputs = -10 V	1,2,3	03	-250	+250	nA
"OFF" switch	-I _{D(OFF)}	$V_D = -10 \text{ V}, V_{EN} = 0.8 \text{ V},$ all unused inputs = +10 V					
Leakage current from an "ON" driver into the	I _{D(ON)}	$V_D = +10 \text{ V}, V_S = +10 \text{ V},$ all unused inputs = -10 V	1,2,3	03	-250	+250	nA
switch (drain)		$V_D = -10 \text{ V}, V_S = -10 \text{ V},$ all unused inputs = +10 V					
Overvoltage protected, leakage current into the	I _{D(OFF)}	$V_S = +25 \text{ V}, V_D = 0 \text{ V},$	1,3	03	-2.0	2.0	μΑ
drain terminal of an "OFF" switch	over- voltage	V _{EN} = 0.8 V	2		-5.0	5.0	-
		V _S = -25 V, V _D = 0 V,	1,3		-2.0	2.0	
		V _{EN} = 0.8 V	2		-5.0	5.0	
Positive supply current	l(+)	V _A = 5.0 V	1,2,3	03		+2.0	mA
Negative supply current	I(-)	V _A = 5.0 V	1,2,3	03		-1.4	mA
Standby positive supply current	+I _{SBY}	V _A = 0 V, V _{EN} = 0.8 V	1, 2, 3	03		+2.0	mA
Standby negative supply current	-I _{SBY}	V _A = 0 V, V _{EN} = 0.8 V	1, 2, 3	03		-1.0	mA

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TABLE I. <u>Electrical performance characteristics</u> – continued.

Test	Symbol	Conditions $\underline{1}$ / V- = -15 V, V+ = +15 V, VEN = 2.4 V	Group A subgroups	Device type	Liı	mits	Unit
		$-55^{\circ}C \le T_{A} \le +125^{\circ}C$ unless otherwise specified			Min	Max	-
Switch "ON" resistance	R _{DS1}	$V_S = +10 \text{ V}, I_D = +100 \mu\text{A}$	1,3	03		1500	Ω
			2	-		1800	
		V _S = -10 V, I _D = -100 μA	1,3			1500	Ω
			2	-		1800	
Switch "ON" resistance	R _{DS2}	V+ = +10 V, V- = -10 V, V _S = +5 V, I _D = +100 μA	1,2,3	03		2200	Ω
		V+ = +10 V, V- = +10 V, $V_S = -5 \text{ V}, I_D = -100 \mu\text{A}$				2200	
Capacitance: Address	C _A	V+ = V- = 0 V, 3/ $f = 1 MHz, T_A = +25^{\circ}C$	4	03		10	pF
Capacitance: output switch	C _{OS}	V+ = V- = 0 V, <u>3</u> / f = 1 MHz, T _A = +25°C	4	03		45	pF
Capacitance: input switch	C _{IS}	$V+ = V- = 0 V, \underline{3}/$ $f = 1 MHz, T_A = +25^{\circ}C$	4	03		10	pF
Charge transfer error	VCTE	$V_S = GND$, $3/$ $V_{GEN} = 0 V \text{ to 5 V}$, $T_A = +25^{\circ}C$	4	03		10	mV
Single channel isolation	V _{ISO}	$V_{GEN} = 1 V_{P-P}, 3/$ f = 200 kHz, $T_A = +25$ °C	4	03	50		dB
Crosstalk between channels	Vст	V _{GEN} = 1 V _{P-P} , <u>3/</u> f = 200 kHz, T _A = +25°C	4	03	50		dB
Break-before-make time delay	t _D	$T_A = +25^{\circ}C$, see figure 3 $3/$	9	03	5		ns
Propagation delay times: Address inputs to	t _{ON(A)}	$R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}, \ \underline{3}/$	9	03		1000	ns
I/O channels	tOFF(A)	see figure 4	10,11			1500	
Enable to I/O	t _{ON(EN)}	$R_L = 1 \text{ k}\Omega, C_L = 100 \text{ pF}, \ \underline{3}$	9	03		1000	ns
	tOFF(EN)	see figure 5	10,11	1		1500	

Unless otherwise specified, V+ = +15 V and V- = -15 V. Input current of one input node. Guaranteed, if not tested, to the limits specified.

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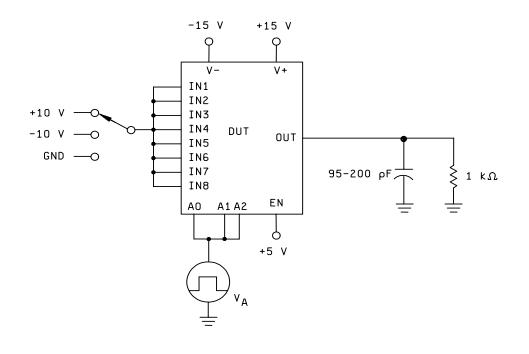
Case outlines	Е	F and X	2			
Device types	01,02,03	01	01,02,03			
Terminal number		Terminal symbol				
1	A0	A0 A0				
2	ENABLE	ENABLE	A0			
3	V-	V-	ENABLE			
4	IN 1	IN 1	V-			
5	IN 2	IN 2	IN 1			
6	IN 3	IN 3	NC			
7	IN 4	IN 4	IN 2			
8	OUT	OUT	IN 3			
9	IN 8	IN 8	IN 4			
10	IN 7	IN 7	OUT			
11	IN 6	IN 6	NC			
12	IN 5	IN 5	IN 8			
13	V+	V+	IN 7			
14	GND	GND	IN 6			
15	A2	A2	IN 5			
16	A1	A1	NC			
17			V+			
18			GND			
19			A2			
20			A1			

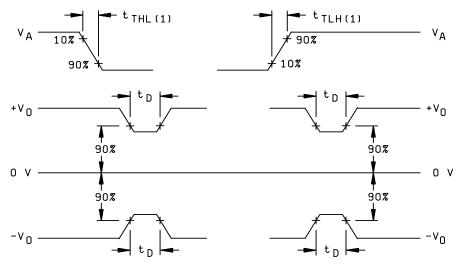
FIGURE 1. <u>Terminal connections</u>.

A2	A1	A0	EN	Channel selected
Х	X	Х	L	None
L	L	L	Н	1
L	L	Н	Н	2
L	Н	L	Н	3
L	Н	Н	Н	4
Н	L	L	Н	5
Н	L	Н	Н	6
Н	Н	L	Н	7
Н	Н	Н	Н	8

FIGURE 2. Truth table.

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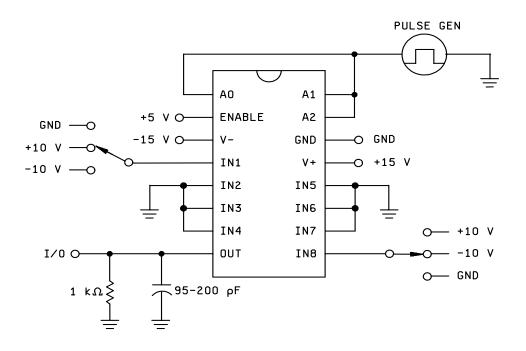


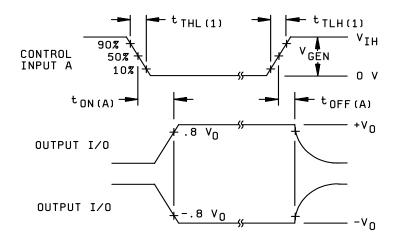
NOTE:

Input pulse requirements: $V_{GEN} = 4 \text{ V}, t_{THL(1)} = t_{TLH(1)} \le 20 \text{ ns}.$

FIGURE 3. Break before make test circuit and waveforms.

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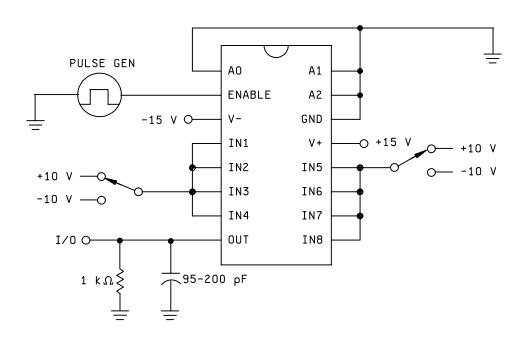


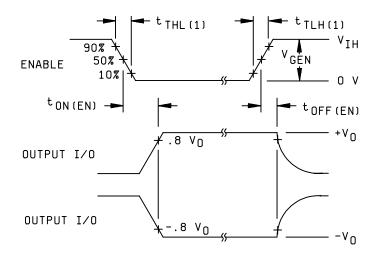
NOTE:

Input pulse requirements: $V_{GEN} = 4 \text{ V}$, $t_{THL(1)} = t_{TLH(1)} \le 20 \text{ ns}$.

FIGURE 4. Timing test circuit and waveforms. (Address inputs to I/O)

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NOTE:

Input pulse requirements: $V_{GEN} = 4 \text{ V}$, $t_{THL(1)} = t_{TLH(1)} \le 20 \text{ ns}$.

FIGURE 5. Timing test circuit and waveforms. (Enable to I/O)

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4. VERIFICATION

- 4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 <u>Quality conformance inspection</u>. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.
 - 4.3.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 5, 6, 7, and 8 in table I, method 5005 of MIL-STD-883 shall be omitted.
 - Subgroup 4 (capacitance measurement) shall be measured only for the initial test and after process or design changes which may affect input capacitance.
 - 4.3.2 Groups C and D inspections.
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. Steady-state life test conditions, method 1005 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - (2) $T_A = +125$ °C, minimum.
 - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)
Interim electrical parameters (method 5004)	1
Final electrical test parameters (method 5004)	1*,2,3,4,9
Group A test requirements (method 5005)	1,2,3,4,9,10**,11**
Groups C and D end-point electrical parameters (method 5005)	1

- * PDA applies to subgroup 1.
- ** Subgroups 10 and 11, if not tested, shall be guaranteed to the specified limits in table I.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535, appendix A.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.2 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.
- 6.4 <u>Record of users</u>. Military and industrial users shall inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and the applicable SMD. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.
- 6.5 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.
- 6.6 <u>Approved sources of supply</u>. Approved sources of supply are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 05-04-05

Approved sources of supply for SMD 77052 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DSCC maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN 1/	Vendor CAGE number	Vendor similar PIN <u>2</u> /	Reference military specification part number
77052012A	24355	ADG508ATE/883B	
	34371	HI4-508/883	
	<u>3</u> /	DG508AAZ/883	
77052012C	1ES66	DG508AAZ/883B	
7705201EA	1ES66	DG508AAK/883B	M38510/19007BEA
	24355	ADG508ATQ/883B	
	<u>3</u> /	HI1-508/883	
	<u>3</u> /	DG508AAP/883	
7705201FA	<u>3</u> /	DG508AAL/883	
7705201XA	<u>3</u> /	DG508AAL/883	
7705201XC	1ES66	DG508AAL/883B	
77052022A	34371	HI4-548/883	
7705202EA	34371	HI1-548/883	M38510/19005BEA
77052032C	1ES66	MAX358MLP/883B	
7705203EA	1ES66	MAX358MJE/883B	M38510/19005BEA

^{1/} The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.

<u>2</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

^{3/} Not available from an approved source of supply.

STANDARD MICROCIRCUIT DRAWING BULLETIN - CONTINUED.

Vendor CAGEVendor namenumberand address

1ES66 Maxim Integrated Products

120 San Gabriel Dr.

Sunnyvale, CA 94086-5125

24533 Analog Devices

Rt 1 Industrial Park PO Box 9106 Norwood, MA 02062

Point of contact: (35361)495999

Raheen Business Park Limerick, Ireland

34371 Intersil Corporation

2401 Palm Bay Blvd

PO Box 883

Melbourne, FL 32902-0883

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